

TSMC-01-1132

February 9, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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Subject:

Serial No. 10/730,778 12/09/03
Yee-Chia Yeo et al.

COMPLEMENTARY METAL OXIDE SEMI-
CONDUCTOR TRANSISTOR TECHNOLOGY
USING SELECTIVE EPITAXY OF A
STRAINED SILICON GERMANIUM LAYER

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

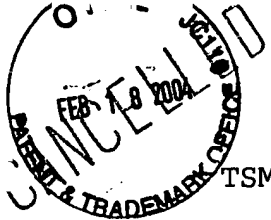
The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

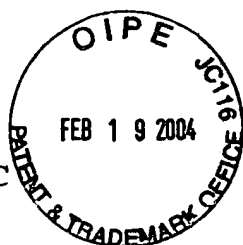
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Stephen B. Ackerman, Reg.# 37761

Signature/Date SB Ackerman 2/17/04



TSMC-01-1132C



U.S. Patent 5,534,713 to Ismail et al., "Complementary Metal-Oxide Semiconductor Transistor Logic Using Strained SI/SIGE Heterostructure Layers," describes the use of thick buffer layers, used with a SiGe layer.

U.S. Patent 5,019,882 to Solomon et al., "Germanium Channel Silicon MOSFET," discloses a Ge channel Si MOSFET process.

U.S. Patent 6,004,137 to Crabbe et al., "Method of Making Graded Channel Effect Transistor," discloses a SixGe1-x graded channel effect Tx.

U.S. Patent 5,985,703 to Banerjee, "Method of Making Thin Film Transistors," discloses a Tx using SixGe1-x layers.

U.S. Patent 5,241,197 to Murakami et al., "Transistor Provided with Strained Germanium Layer," discloses FET's with SixGe1-x layers.

U.S. Patent 5,981,345 to Ryum et al., "FI/SIGE MOSFET and Method for Fabricating the Same," discloses a SixGe1-x channel.

Sincerely,

Stephen B. Ackerman,
Reg. No. 37761

OIPE
FEB 18 2004
CANCELED
FEB 19 2004
PATENT & TRADEMARK OFFICE

Form PTO-1449	Docket Number (Optional) TSMC-01-1132C	Application Number 10/730,778
INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)		
Applicant Yee-Chia Yeo et al.		Group Art Unit
Filing Date 12/09/03		

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	5534713	7/9/96	Ismail et al.	257	24	5/20/94
	5019882	5/28/91	Solomon et al.	357	23.8	5/15/89
	6004137	12/21/99	Crabbé et al.	437	40	9/23/93
	5985703	11/16/99	Banerjee	438	162	5/13/96
	5241197	8/31/93	Murakami et al.	257	192	9/13/91
	5981345	11/9/99	Ryum et al.	438	303	7/10/97

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portmox Pages, Etc.)

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.